What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f405rgt6tr

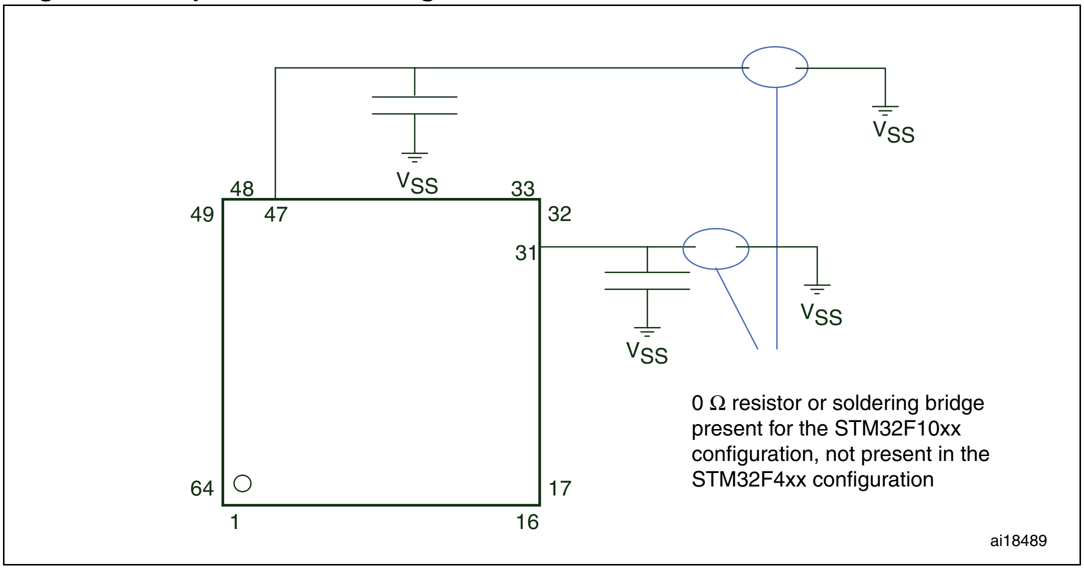
2.1 Full compatibility throughout the family

The STM32F405xx and STM32F407xx are part of the STM32F4 family. They are fully pin-to-pin, software and feature compatible with the STM32F2xx devices, allowing the user to try different memory densities, peripherals, and performances (FPU, higher frequency) for a greater degree of freedom during the development cycle.

The STM32F405xx and STM32F407xx devices maintain a close compatibility with the whole STM32F10xxx family. All functional pins are pin-to-pin compatible. The STM32F405xx and STM32F407xx, however, are not drop-in replacements for the STM32F10xxx devices: the two families do not have the same power scheme, and so their power pins are different. Nonetheless, transition from the STM32F10xxx to the STM32F40xxx family remains simple as only a few pins are impacted.

Figure 4, *Figure 3*, *Figure 2*, and *Figure 1* give compatible board designs between the STM32F40xxx, STM32F2, and STM32F10xxx families.

Figure 1. Compatible board design between STM32F10xx/STM32F40xxx for LQFP64



Two external ceramic capacitors should be connected on V_{CAP_1} & V_{CAP_2} pin. Refer to *Figure 21: Power supply scheme* and *Figure 16: VCAP_1/VCAP_2 operating conditions*.

All packages have regulator ON feature.

Regulator OFF

This feature is available only on packages featuring the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V_{12} voltage source through V_{CAP_1} and V_{CAP_2} pins.

Since the internal voltage scaling is not manage internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to *Table 14: General operating conditions*.

The two 2.2 µF ceramic capacitors should be replaced by two 100 nF decoupling capacitors.

Refer to *Figure 21: Power supply scheme*

When the regulator is OFF, there is no more internal monitoring on V_{12}. An external power supply supervisor should be used to monitor the V_{12} of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V_{12} power domain.

In regulator OFF mode the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V_{12} logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The standby mode is not available

Figure 9. Regulator OFF

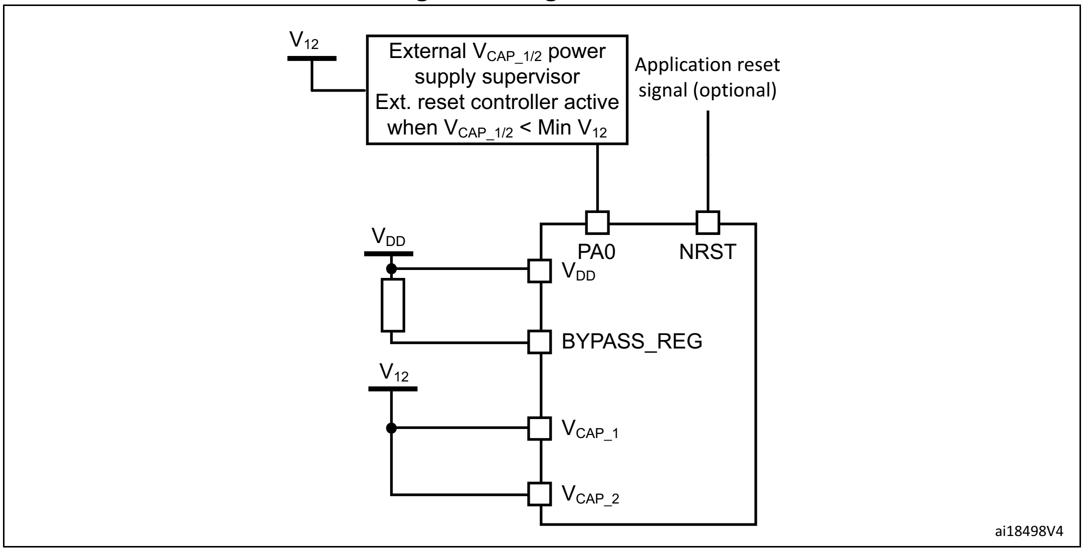
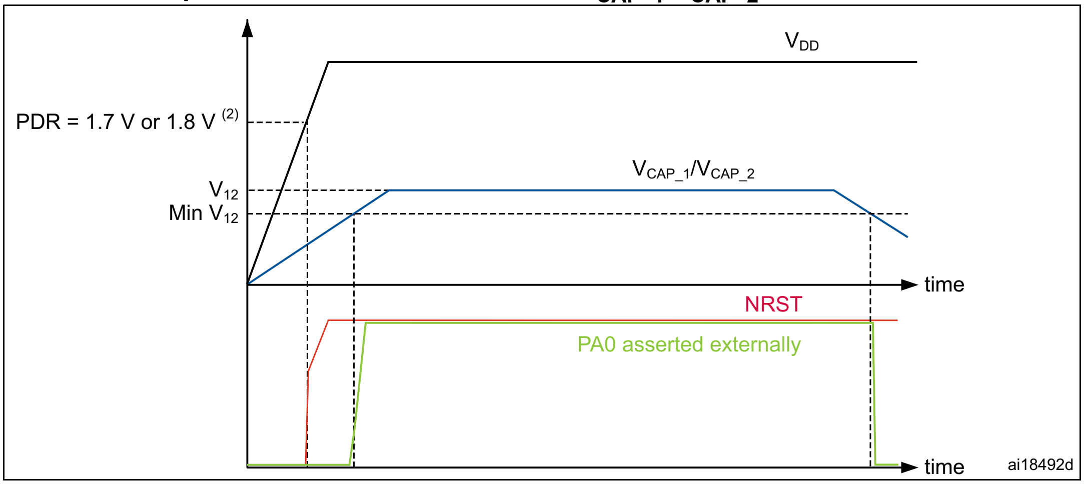


Figure 11. Startup in regulator OFF mode: fast V_{DD} slope - power-down reset risen before V_{CAP_1}/V_{CAP_2} stabilization



1. This figure is valid both whatever the internal reset mode (ON or OFF).
2. PDR = 1.7 V for a reduced temperature range; PDR = 1.8 V for all temperature ranges.

2.2.17 Regulator ON/OFF and internal reset ON/OFF availability

Table 3. Regulator ON/OFF and internal reset ON/OFF availability

<table>
<tr><th></th><th>Regulator ON</th><th>Regulator OFF</th><th>Internal reset ON</th><th>Internal reset OFF</th></tr>
<tr><td>LQFP64
LQFP100</td><td rowspan="2">Yes</td><td rowspan="2">No</td><td>Yes</td><td>No</td></tr>
<tr><td>LQFP144</td><td rowspan="2">Yes
PDR_ON set to V_{DD}</td><td rowspan="2">Yes
PDR_ON connected to an external power supply supervisor</td></tr>
<tr><td>WLCSP90
UFBGA176
LQFP176</td><td>Yes
BYPASS_REG set to V_{SS}</td><td>Yes
BYPASS_REG set to V_{DD}</td></tr>
</table>

2.2.18 Real-time clock (RTC), backup SRAM and backup registers

The backup domain of the STM32F405xx and STM32F407xx includes:

- The real-time clock (RTC)
- 4 Kbytes of backup SRAM
- 20 backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (in 12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are performed automatically. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes. The sub-seconds value is also available in binary format.

It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC

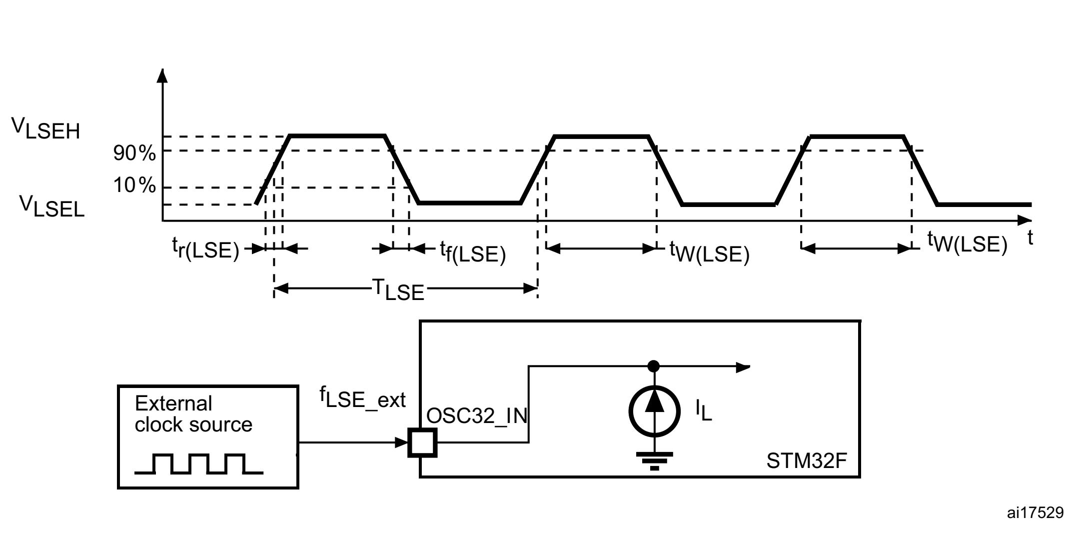
Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
11	E9	18	29	M5	35	PC3	I/O	FT	(4)	SPI2_MOSI / I2S2_SD / OTG_HS_ULPI_NXT / ETH_MII_TX_CLK/ EVENTOUT	ADC123_IN13
-	-	19	30	-	36	V_{DD}	S	-	-	-	-
12	H10	20	31	M1	37	V_{SSA}	S	-	-	-	-
-	-	-	-	N1	-	V_{REF-}	S	-	-	-	-
-	-	21	32	P1	38	V_{REF+}	S	-	-	-	-
13	G9	22	33	R1	39	V_{DDA}	S	-	-	-	-
14	C10	23	34	N3	40	PA0/WKUP (PA0)	I/O	FT	(5)	USART2_CTS/ UART4_TX/ ETH_MII_CRS / TIM2_CH1_ETR/ TIM5_CH1 / TIM8_ETR/ EVENTOUT	ADC123_IN0/WKUP(4)
15	F8	24	35	N2	41	PA1	I/O	FT	(4)	USART2_RTS / UART4_RX/ ETH_RMII_REF_CLK / ETH_MII_RX_CLK / TIM5_CH2 / TIM2_CH2/ EVENTOUT	ADC123_IN1
16	J10	25	36	P2	42	PA2	I/O	FT	(4)	USART2_TX/TIM5_CH3 / TIM9_CH1 / TIM2_CH3 / ETH_MDIO/ EVENTOUT	ADC123_IN2
-	-	-	-	F4	43	PH2	I/O	FT	-	ETH_MII_CRS/EVENTOUT	-
-	-	-	-	G4	44	PH3	I/O	FT	-	ETH_MII_COL/EVENTOUT	-
-	-	-	-	H4	45	PH4	I/O	FT	-	I2C2_SCL / OTG_HS_ULPI_NXT/ EVENTOUT	-
-	-	-	-	J4	46	PH5	I/O	FT	-	I2C2_SDA/ EVENTOUT	-
17	H9	26	37	R2	47	PA3	I/O	FT	(4)	USART2_RX/TIM5_CH4 / TIM9_CH2 / TIM2_CH4 / OTG_HS_ULPI_D0 / ETH_MII_COL/ EVENTOUT	ADC123_IN3
18	E5	27	38	-	-	V_{SS}	S	-	-	-	-

Table 10. register boundary addresses (continued)

Bus	Boundary address	Peripheral
AHB1	0x4004 0000 - 0x4007 FFFF	USB OTG HS
	0x4002 9400 - 0x4003 FFFF	Reserved
	0x4002 9000 - 0x4002 93FF	ETHERNET MAC
	0x4002 8C00 - 0x4002 8FFF	
	0x4002 8800 - 0x4002 8BFF	
	0x4002 8400 - 0x4002 87FF	
	0x4002 8000 - 0x4002 83FF	
	0x4002 6800 - 0x4002 7FFF	Reserved
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0x4002 5000 - 0x4002 5FFF	Reserved
	0x4002 4000 - 0x4002 4FFF	BKPSRAM
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
	0x4002 3800 - 0x4002 3BFF	RCC
	0x4002 3400 - 0x4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
	0x4002 2400 - 0x4002 2FFF	Reserved
	0x4002 2000 - 0x4002 23FF	GPIOI
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1800 - 0x4002 1BFF	GPIOG
	0x4002 1400 - 0x4002 17FF	GPIOF
	0x4002 1000 - 0x4002 13FF	GPIOE
	0x4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA
	0x4001 5800- 0x4001 FFFF	Reserved

Figure 31. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 32*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

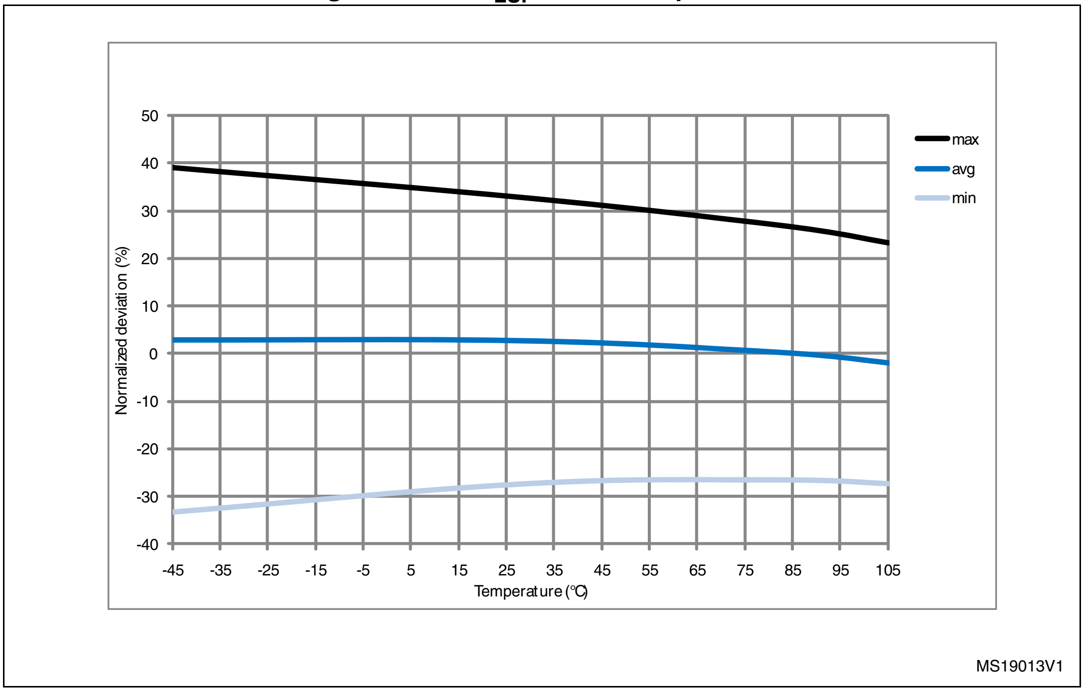
Table 32. HSE 4-26 MHz oscillator characteristics (1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	4	-	26	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
G_m	Oscillator transconductance	Startup	5	-	-	mA/V
$G_{mcritmax}$	Maximum critical crystal G_m	Startup	-	-	1	mA/V
$t_{SU(HSE)}$(2)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. Guaranteed by characterization. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 32*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Figure 34. ACC_{LSI} versus temperature



5.3.10 PLL characteristics

The parameters given in *Table 36* and *Table 37* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 36. Main PLL characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock(1)	-	0.95(2)	1	2.10	MHz
f_{PLL_OUT}	PLL multiplier output clock	-	24	-	168	MHz
f_{PLL48_OUT}	48 MHz PLL multiplier output clock	-	-	48	75	MHz
f_{VCO_OUT}	PLL VCO output	-	100	-	432	MHz
t_{LOCK}	PLL lock time	VCO freq = 100 MHz	75	-	200	µs
		VCO freq = 432 MHz	100	-	300	

Table 41. Flash memory programming with V_{PP}

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Double word programming	T_A = 0 to +40 °C V_{DD} = 3.3 V V_{PP} = 8.5 V	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time		-	230	-	ms
$t_{ERASE64KB}$	Sector (64 KB) erase time		-	490	-	
$t_{ERASE128KB}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	6.9	-	s
V_{prog}	Programming voltage	-	2.7	-	3.6	V
V_{PP}	V_{PP} voltage range	-	7	-	9	V
I_{PP}	Minimum current sunk on the V_{PP} pin	-	10	-	-	mA
t_{VPP}(3)	Cumulative time during which V_{PP} is applied	-	-	-	1	hour

1. Guaranteed by design.
2. The maximum programming time is measured after 100K erase operations.
3. V_{PP} should only be connected during programming/erasing.

Table 42. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycles(2) at T_A = 55 °C	20	

1. Guaranteed by characterization.
2. Cycling performed over the whole temperature range.

5.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC? code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 44. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{CPU}] 25/168 MHz	Unit
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running from Flash with ART accelerator enabled	0.1 to 30 MHz	32	dBµV
			30 to 130 MHz	25	
			130 MHz to 1GHz	29	
			SAE EMI Level	4	-
		V_{DD} = 3.3 V, T_A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running from Flash with ART accelerator and PLL spread spectrum enabled	0.1 to 30 MHz	19	dBµV
			30 to 130 MHz	16	
			130 MHz to 1GHz	18	
			SAE EMI level	3.5	-

5.3.14 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 45. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C conforming to JESD22-A114	2	2000(2)	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C conforming to ANSI/ESD STM5.3.1	II	500	

1. Guaranteed by characterization.
2. On V_{BAT} pin, $V_{ESD(HBM)}$ is limited to 1000 V.

5.3.17 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 48*).

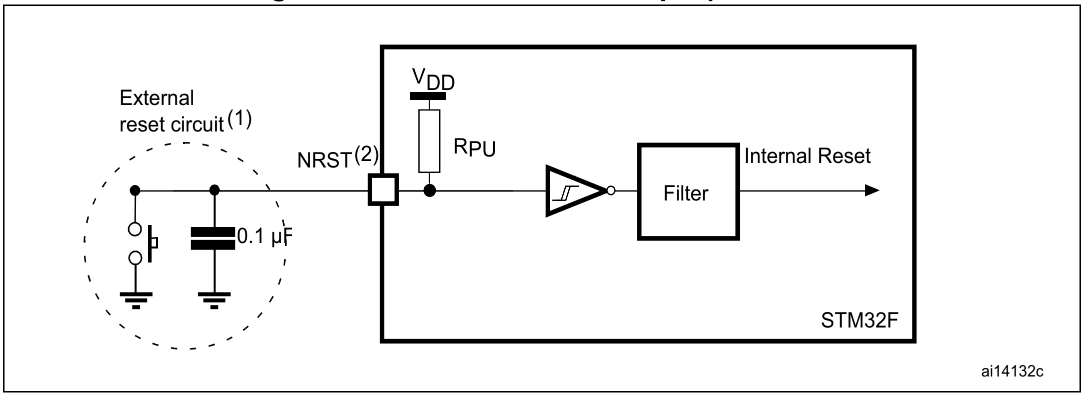
Unless otherwise specified, the parameters given in *Table 51* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 51. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$(1)	NRST Input low level voltage	TTL ports $2.7\ V \le V_{DD} \le 3.6\ V$	-	-	0.8	V
$V_{IH(NRST)}$(1)	NRST Input high level voltage		2	-	-	
$V_{IL(NRST)}$(1)	NRST Input low level voltage	CMOS ports $1.8\ V \le V_{DD} \le 3.6\ V$	-	-	$0.3V_{DD}$	
$V_{IH(NRST)}$(1)	NRST Input high level voltage		$0.7V_{DD}$	-	-	
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor(2)	$V_{IN} = V_{SS}$	30	40	50	kΩ
$V_{F(NRST)}$(1)	NRST Input filtered pulse		-	-	100	ns
$V_{NF(NRST)}$(1)	NRST Input not filtered pulse	$V_{DD} > 2.7\ V$	300	-	-	ns
T_{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	-	µs

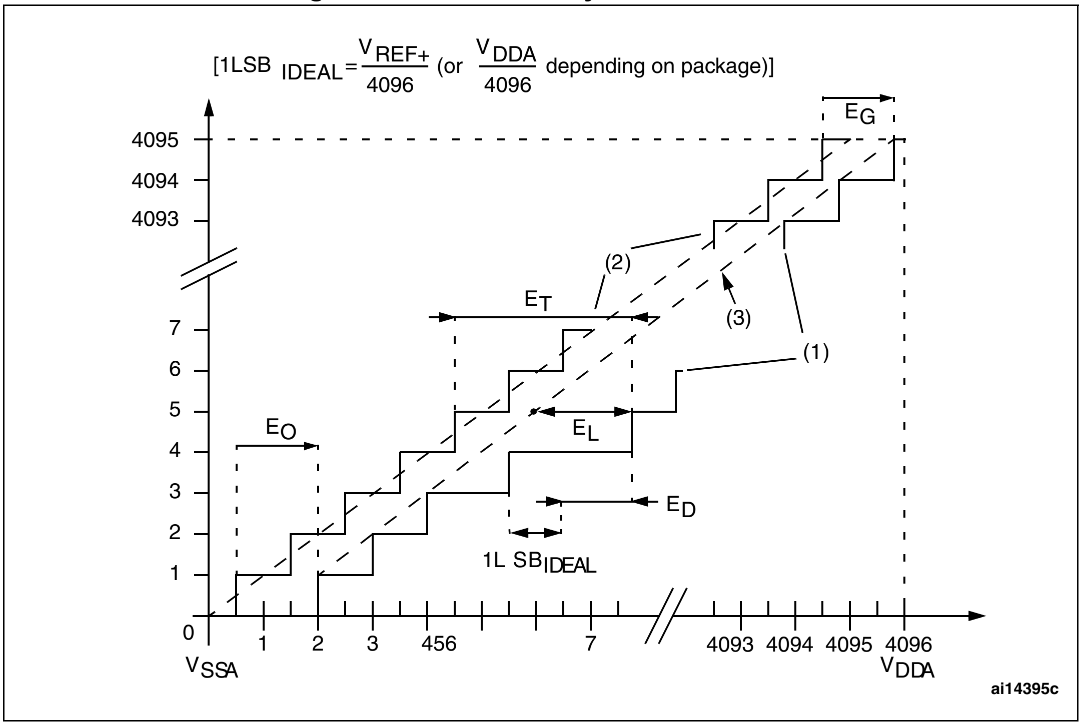
1. Guaranteed by design.
2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

Figure 38. Recommended NRST pin protection



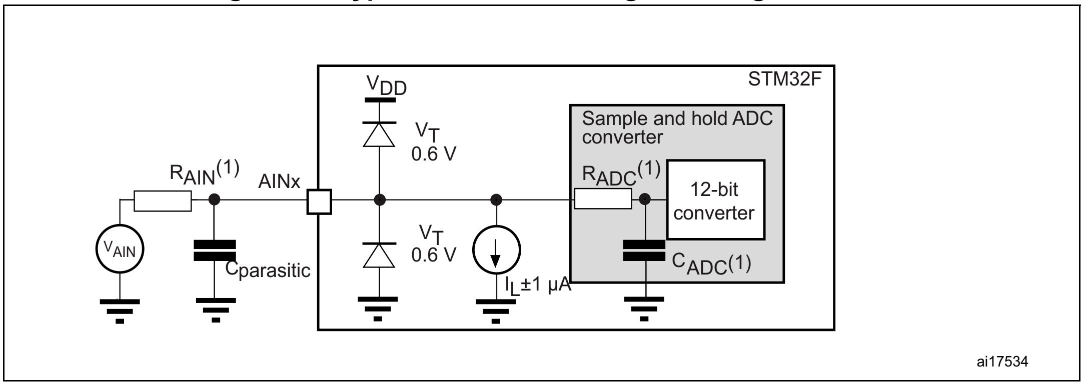
1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 51*. Otherwise the reset is not taken into account by the device.

Figure 49. ADC accuracy characteristics



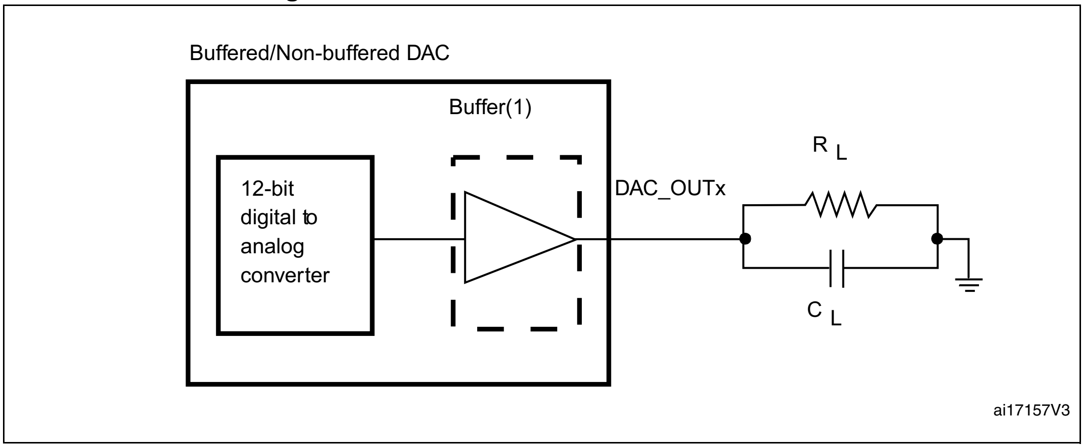
1. See also *Table 68*.
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
   EO = Offset Error: deviation between the first actual transition and the first ideal one.
   EG = Gain Error: deviation between the last ideal transition and the last actual one.
   ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
   EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 50. Typical connection diagram using the ADC



1. Refer to *Table 67* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

Figure 53. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

5.3.26 FSMC characteristics

Unless otherwise specified, the parameters given in *Table 75* to *Table 86* for the FSMC interface are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in *Table 14*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to Section *Section 5.3.16: I/O port characteristics* for more details on the input/output characteristics.

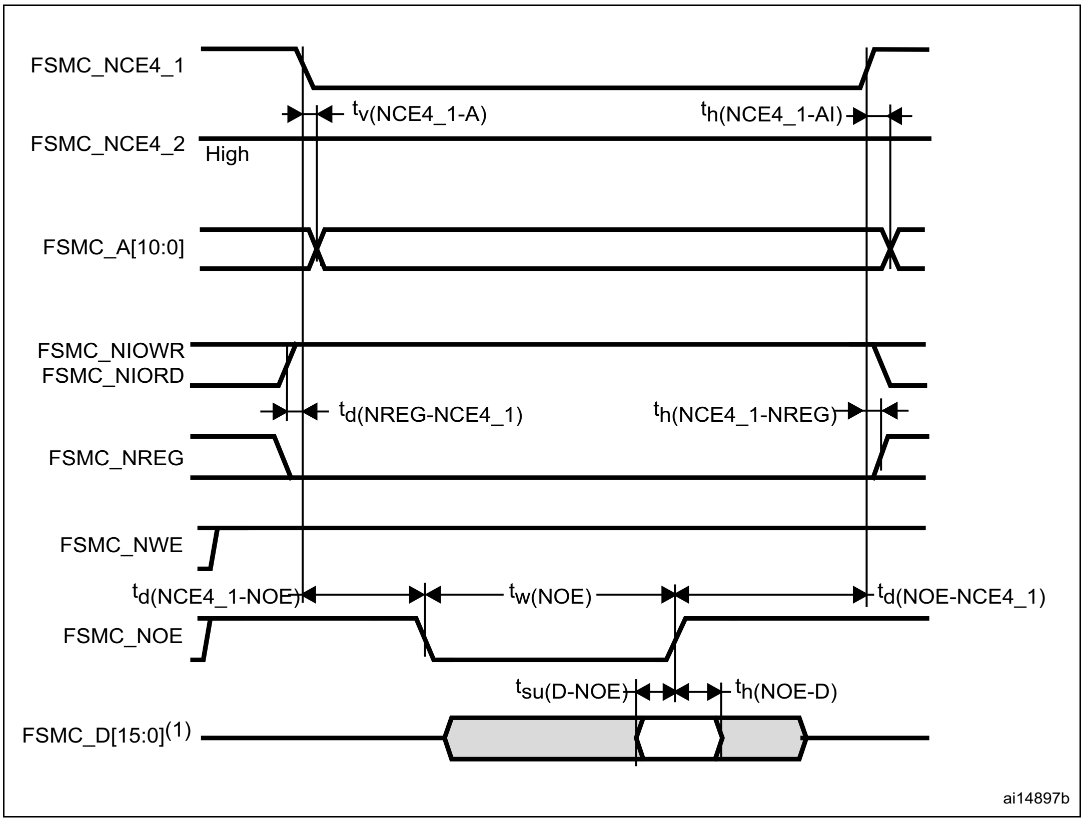
Asynchronous waveforms and timings

Figure 54 through *Figure 57* represent asynchronous waveforms and *Table 75* through *Table 78* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- AddressSetupTime = 1
- AddressHoldTime = 0x1
- DataSetupTime = 0x1
- BusTurnAroundDuration = 0x0

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 64. PC Card/CompactFlash controller waveforms for attribute memory read access



1. Only data bits 0...7 are read (bits 8...15 are disregarded).

Figure 67. PC Card/CompactFlash controller waveforms for I/O space write access

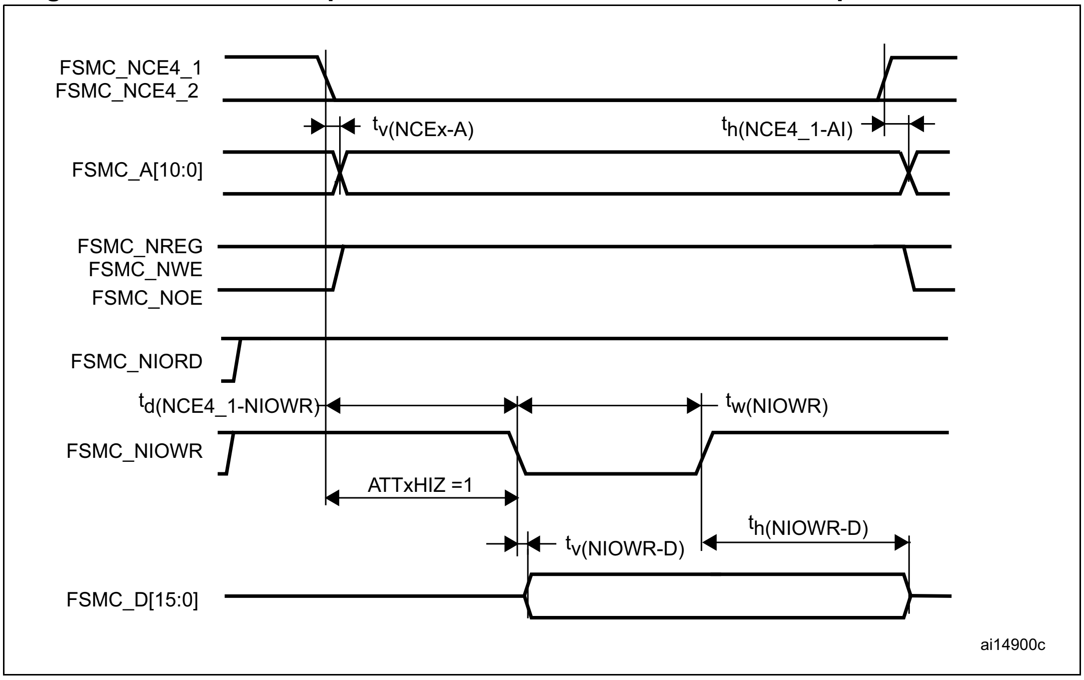


Table 83. Switching characteristics for PC Card/CF read and write cycles in attribute/common space(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$	FSMC_Ncex low to FSMC_Ay valid	-	0	ns
$t_{h(NCEx\_AI)}$	FSMC_NCEx high to FSMC_Ax invalid	4	-	ns
$t_{d(NREG-NCEx)}$	FSMC_NCEx low to FSMC_NREG valid	-	3.5	ns
$t_{h(NCEx-NREG)}$	FSMC_NCEx high to FSMC_NREG invalid	T_{HCLK}+4	-	ns
$t_{d(NCEx-NWE)}$	FSMC_NCEx low to FSMC_NWE low	-	5T_{HCLK}+0.5	ns
$t_{d(NCEx-NOE)}$	FSMC_NCEx low to FSMC_NOE low	-	5T_{HCLK} +0.5	ns
$t_{w(NOE)}$	FSMC_NOE low width	8T_{HCLK}–1	8T_{HCLK}+1	ns
$t_{d(NOE\_NCEx)}$	FSMC_NOE high to FSMC_NCEx high	5T_{HCLK}+2.5	-	ns
$t_{su\ (D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	4.5	-	ns
$t_{h(N0E-D)}$	FSMC_N0E high to FSMC_D[15:0] invalid	3	-	ns
$t_{w(NWE)}$	FSMC_NWE low width	8T_{HCLK}–0.5	8T_{HCLK}+ 3	ns
$t_{d(NWE\_NCEx)}$	FSMC_NWE high to FSMC_NCEx high	5T_{HCLK}–1	-	ns
$t_{d(NCEx-NWE)}$	FSMC_NCEx low to FSMC_NWE low	-	5T_{HCLK}+ 1	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
t_h (NWE-D)	FSMC_NWE high to FSMC_D[15:0] invalid	8T_{HCLK} –1	-	ns
t_d (D-NWE)	FSMC_D[15:0] valid before FSMC_NWE high	13T_{HCLK} –1	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization.

Table 90. WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	0.540	0.570	0.600	0.0213	0.0224	0.0236
A1	-	0.190	-	-	0.0075	-
A2	-	0.380	-	-	0.0150	-
A3(2)	-	0.025	-	-	0.0010	-
b(3)	0.240	0.270	0.300	0.0094	0.0106	0.0118
D	4.188	4.223	4.258	0.1649	0.1663	0.1676
E	3.934	3.969	4.004	0.1549	0.1563	0.1576
e	-	0.400	-	-	0.0157	-
e1	-	3.600	-	-	0.1417	-
e2	-	3.200	-	-	0.1260	-
F	-	0.3115	-	-	0.0123	-
G	-	0.3845	-	-	0.0151	-
aaa	-	0.100	-	-	0.0039	-
bbb	-	0.100	-	-	0.0039	-
ccc	-	0.100	-	-	0.0039	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 76. WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale recommended footprint

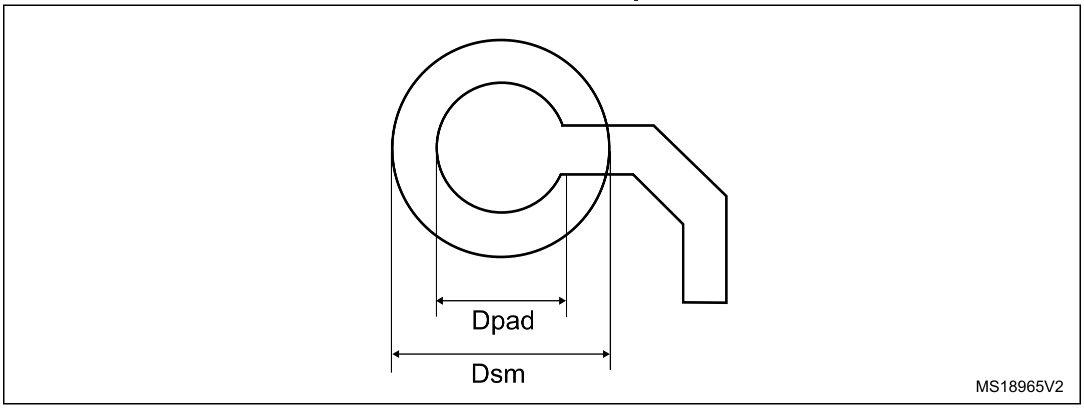
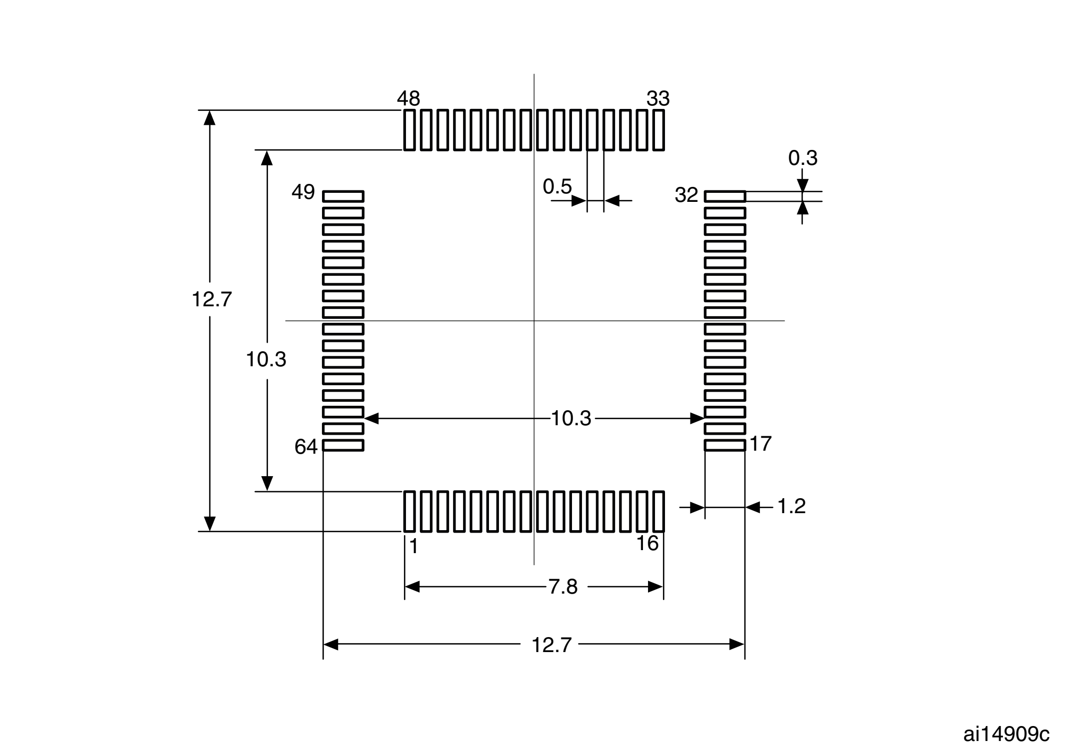


Table 92. LQFP64 – 64-pin 10 x 10 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 79. LQFP64 – 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint



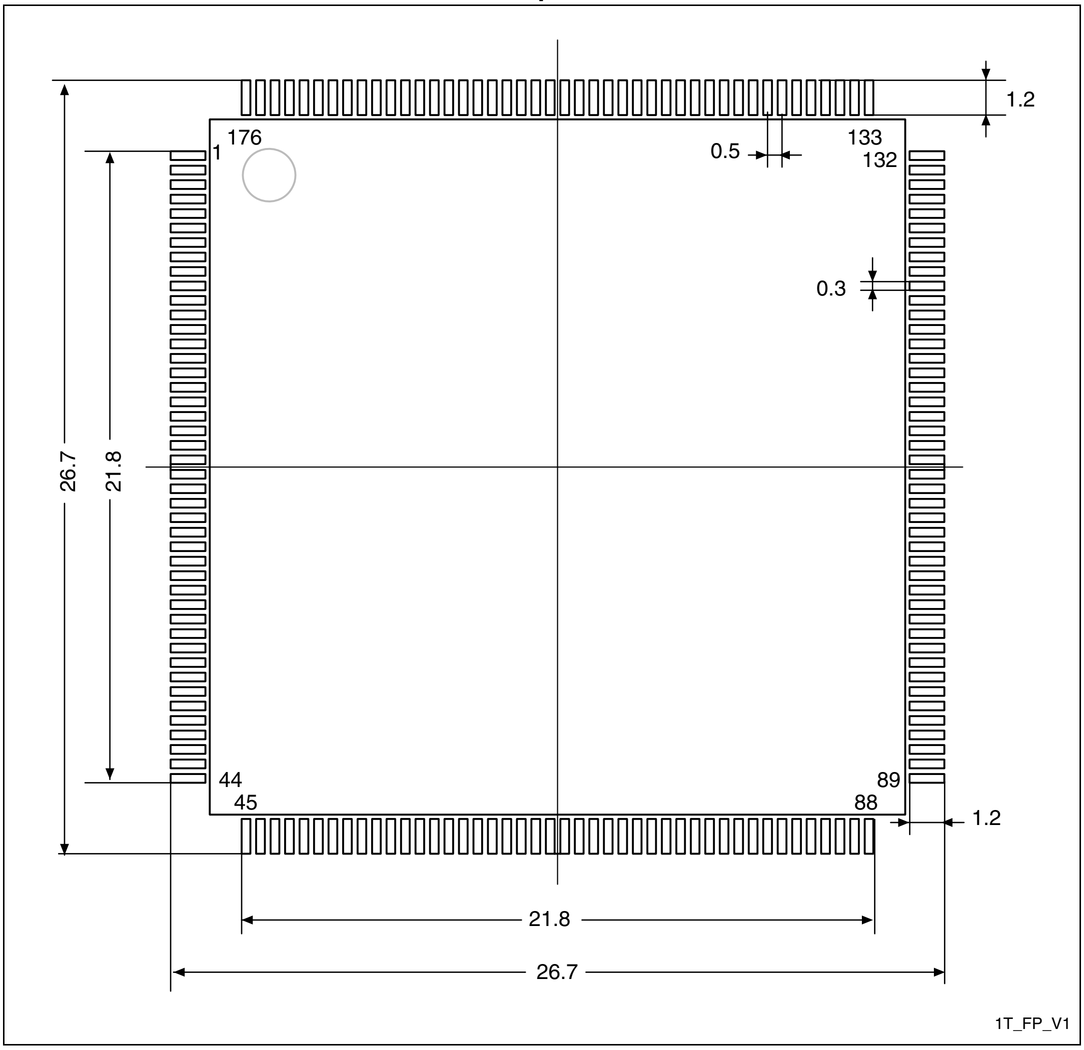
1. Dimensions are in millimeters.

Table 97. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
ZD	-	1.250	-	-	0.0492	-
E	23.900	-	24.100	0.9409	-	0.9488
HE	25.900	-	26.100	1.0197	-	1.0276
ZE	-	1.250	-	-	0.0492	-
e	-	0.500	-	-	0.0197	-
L[2]	0.450	-	0.750	0.0177	-	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	-	7°	0°	-	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. L dimension is measured at gauge plane at 0.25 mm above the seating plane.

Figure 91. LQFP176 - 176-pin, 24 x 24 mm low profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.